

ORDENAGAILUEN TEKNOLOGIAREN OINARRIAK

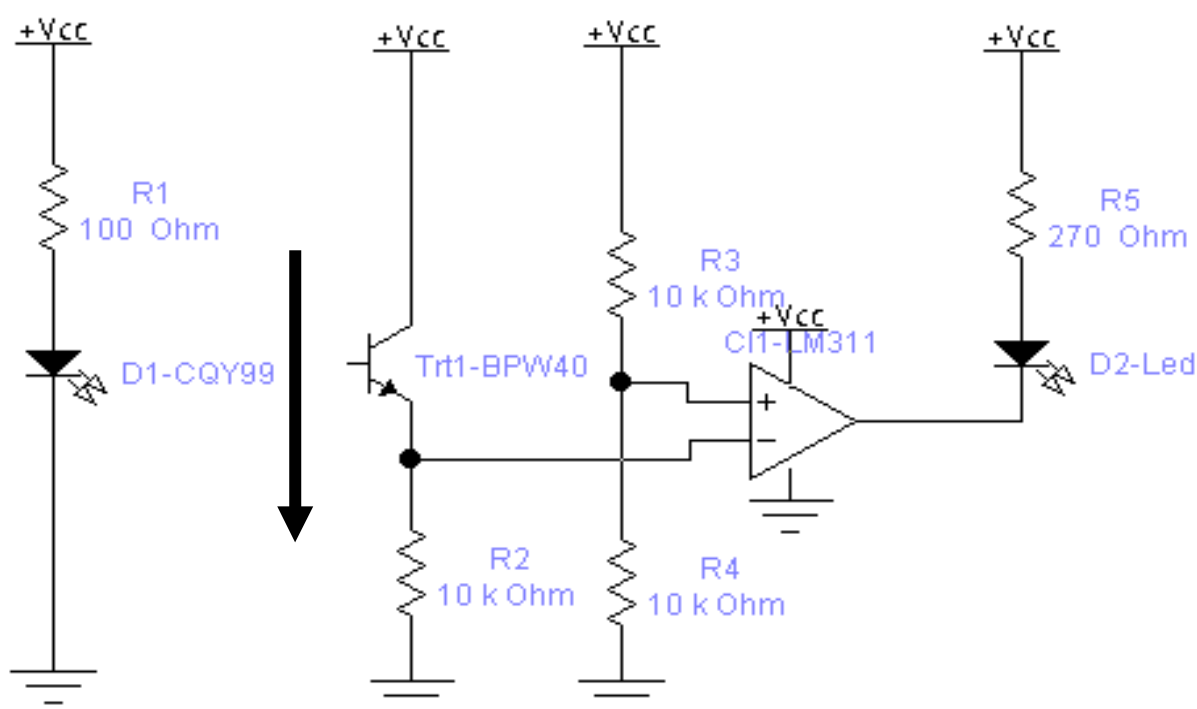
LABORATEGIKO PRAKTIKA

5. Praktika: Fotoigorleak - Fototransistoreak

Hesi fotoelektriko baten muntaia egingo da, fotoigorle bat eta fototransistore (foto-hargailu) baten bidez, biak espektro infragorrian lan egingo dute. Praktika hau, *protoboard*ak muntatzeko mailetan muntatuko da, osagai fisikoekin.

Osagai berria dugu, LM311a, seinale elektrikoaren konparatzailea hain zuzen ere. Konparatzaile honek objektuak antzemango ditu, argi infragorria eteterakoan.

Tentsioen eta korronteen kalkulu teoriko eta praktikoak egingo dira. Horretarako, polimetroa erabiliko da.



Kalkulu eta neurketak:

1. D1 diodoan zehar doan korrontea kalkulatu eta neurtu.
2. Trt1 transistorearen igorlean dagoen tentsioa neurtu, hesia zabalik eta itxita dagoenean.
3. R3 eta R4k sortzen duten korapiloan tentsioa neurtu eta kalkulatu.
4. IC1eko irteerako tentsioa kalkulatu.
5. D2 diodoan zehar doan korrontea kalkulatu eta neurtu.

Osagaien zerrenda:

Erresistoreak	Osagaia
100 Ω	R1
10 K Ω	R2,R3,R4
270 Ω	R5
Fotodiodoak	
L53F3C (gardena)	D1
Fototransistoreak	
L53P3C (gardena)	Trt1
Led diodoak	
Gorria	D2
Zirkuitu Integratuak	
LM311	CI1

Fotoigorlea:

Infragorriko espektroko argia igortzen du kitzikatuta dagoenean. Igorritako argia hobeto fokalizatzeko lente bat dauka.

Fototransistorea:

Argi ikuskorreko eta argi infragorriko erradiazioetara sentikorra da. Bere fokua hobetzeko lentea dauka baita ere..

Konparatzailea:

Bi sarreraren arteko konparaketa egiten du. (+) hankatxoko tentsioa, balio absolutuan (-) hankatxoko tentsioa baino handiagoa bada, irteera inpedantzia altuko egoeran jartzen da, kolektore irekia izanagatik. $V^- > V^+$ balio absolutuan, irteera, 0 da.

L-53F3C	L-53F3BT
L-53SF4C	L-53SF4BT
L-53SF6C	L-53SF6BT
L-53SF7C	L-53SF7BT

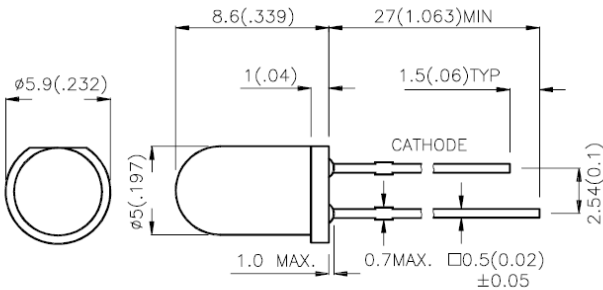
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE L-51P3C PHOTOTRANSISTOR.
- BOTH WATER CLEAR LENS AND BLUE TRANSPARENT LENS AVAILABLE HIGH POWER OUTPUT.

Description

F3 Made with Gallium Arsenide Infrared Emitting diodes.
SF4 and SF6 and SF7 Made with Gallium Aluminum Arsenide Infrared Emitting diodes.

Package Dimensions



- Notes:
1. All dimensions are in millimeters (inches).
 2. Tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
 3. Lead spacing is measured where the lead emerge package.
 4. Specifications are subject to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Po (mW/sr) @20mA		Po (mW/sr) @50mA		Viewing Angle
			Min.	Typ.	Min.	Typ.	2θ1/2
L-53F3C	GaAs	WATER CLEAR	8	20	12	30	30°
L-53F3BT	GaAs	BLUE TRANS.	5	20	8	30	30°
L-53SF4C	GaAlAs	WATER CLEAR	8	20	12	30	30°
L-53SF4BT	GaAlAs	BLUE TRANS.	5	20	8	30	30°
L-53SF6C	GaAlAs	WATER CLEAR	10	40	50	100	30°
L-53SF6BT	GaAlAs	BLUE TRANS.	10	40	50	100	30°
L-53SF7C	GaAlAs	WATER CLEAR	10	40	50	100	30°
L-53SF7BT	GaAlAs	BLUE TRANS.	10	40	50	100	30°

Note:

1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.

Electrical / Optical Characteristics at T_A=25°C

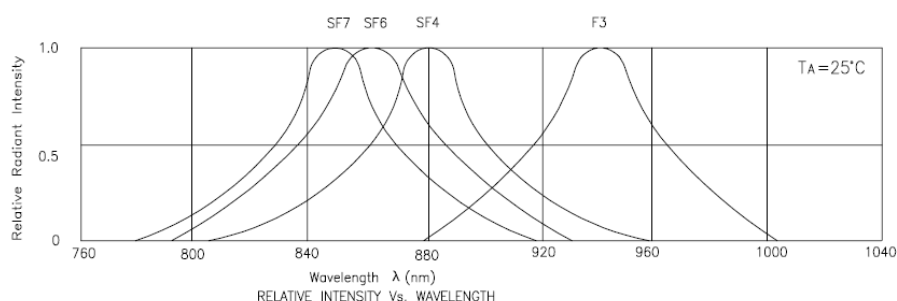
Item	P/N	Symbol	Typ.	Max.	Unit	Condition
Forward Voltage	F3 SF4 SF6 SF7	V _F	1.2 1.3 1.35 1.4	1.5 1.7 1.6 1.8	V	I _F =20mA
Reverse Current	F3 SF4 SF6 SF7	I _R	-	10 10 10 10	μA	V _R =5V
Junction Capacitance	F3 SF4 SF6 SF7	C	90 90 30 30	-	pF	V=0 f=1MHz
Peak Spectral Wavelength	F3 SF4 SF6 SF7	λ _P	940 880 860 850	-	nm	I _F =20mA
Spectral Bandwidth	F3 SF4 SF6 SF7	Δλ	50 50 50 41	-	nm	I _F =20mA

Absolute Maximum Ratings at $T_A=25^{\circ}\text{C}$

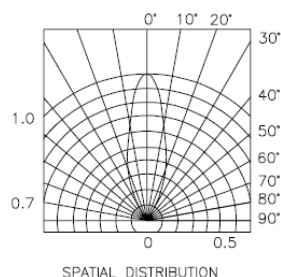
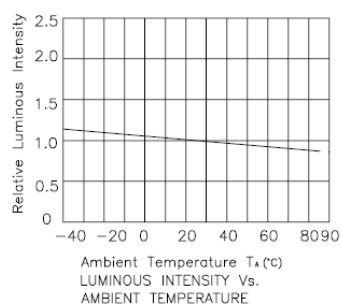
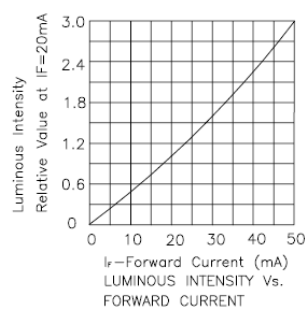
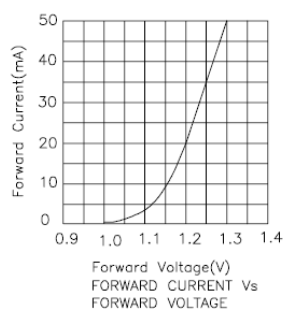
Item	Symbol	F3&SF4	SF6&SF7	Units
Power Dissipation	P_d	100	100	mW
Forward Current	I_F	50	50	mA
Peak Forward Current	I_p	1.2	1	A
Reverse Voltage	V_R	5	5	V
Operating Temperature	T_{opr}	-40~ +85	-40~ +85	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-40~ +85	-40~ +85	$^{\circ}\text{C}$

Notes:

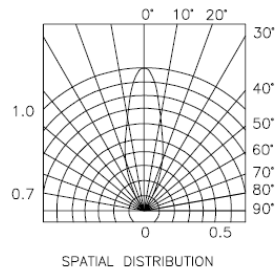
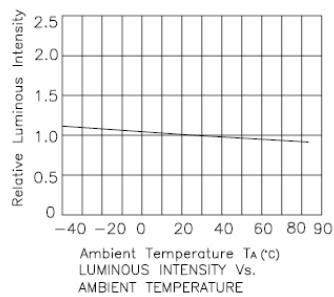
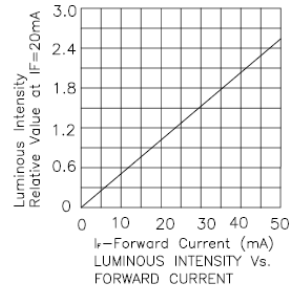
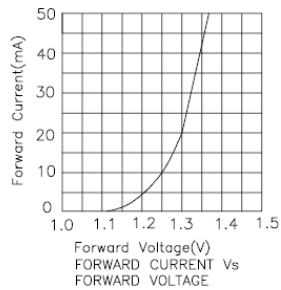
- 1/10 Duty Cycle, 0.1ms Pulse Width.
- 4mm below package base.



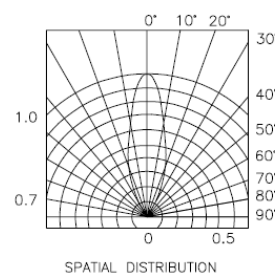
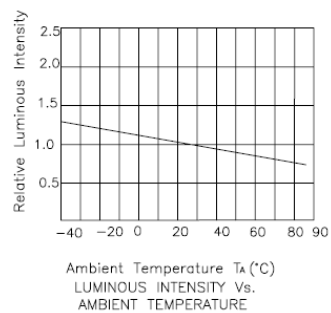
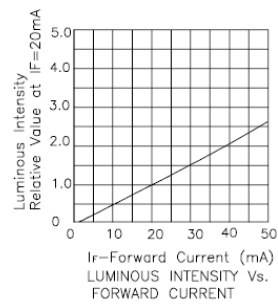
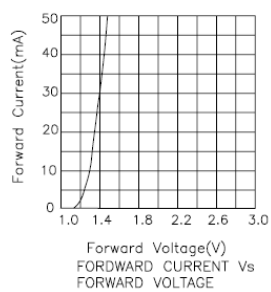
L-53F3C, L-53F3BT



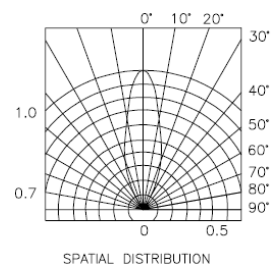
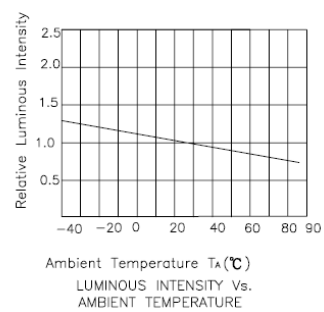
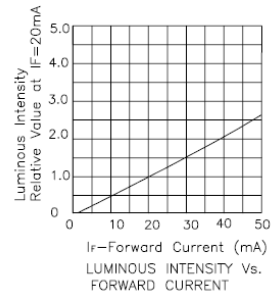
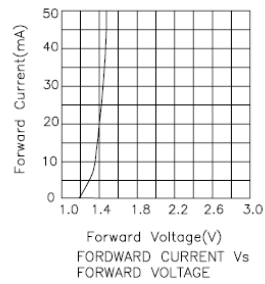
L-53SF4C, L-53SF4BT



L-53SF6C, L-53SF6BT



L-53SF7C, L-53SF7BT



L-53P3C

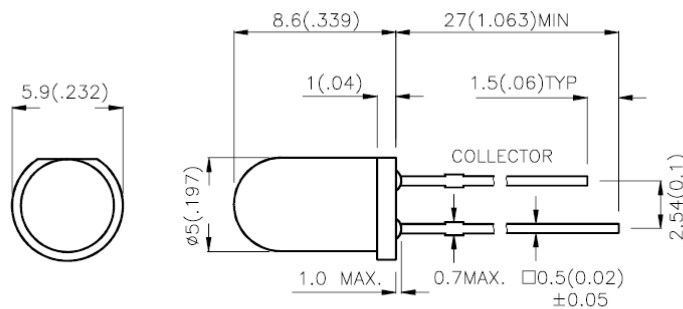
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE L-53 SERIES INFRARED EMITTING LED LAMP.
- WATER CLEAR LENS.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ± 0.25 (0.01") unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Electrical / Optical Characteristics at $T_A=25^{\circ}\text{C}$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
$V_{BR\ CE0}$	Collector-to-Emitter Breakdown Voltage	30	-	-	V	$I_C=100\mu\text{A}$ $E_e=0\text{mW}/\text{cm}^2$
$V_{BR\ ECO}$	Emitter-to-Collector Breakdown Voltage	5	-	-	V	$I_E=100\mu\text{A}$ $E_e=0\text{mW}/\text{cm}^2$
$V_{CE\ (SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	$I_C=2\text{mA}$ $E_e=20\text{mW}/\text{cm}^2$
I_{CE0}	Collector Dark Current	-	-	100	nA	$V_{CE}=10\text{V}$ $E_e=0\text{mW}/\text{cm}^2$
T_R	Rise Time (10% to 90%)	-	3	-	us	$V_{CE}=5\text{V}$ $I_C=1\text{mA}$ $R_L=1000\Omega$
T_F	Fall Time (90% to 10%)	-	3	-	us	
$I_{(ON)}$	On State Collector Current	0.1	0.5	-	mA	$V_{CE}=5\text{V}$ $E_e=1\text{mW}/\text{cm}^2$ $\lambda=940\text{nm}$

Absolute Maximum Ratings at $T_A=25^{\circ}\text{C}$

Parameter	Maximum Rating
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	$-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$
Storage Temperature Range	$-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$
Lead soldering Temperature ($>5\text{mm}$ for 5sec)	260°C

DATA SHEET

LM111/211/311/311B Voltage comparator

Product data
Supersedes data of 1994 Aug 31
File under Integrated Circuits, IC11 Handbook

2001 Aug 03



Voltage comparator

LM111/211/311/311B

DESCRIPTION

The LM111 series are voltage comparators that have input currents approximately a hundred times lower than devices like the $\mu\text{A}710$. They are designed to operate over a wider range of supply voltages; from standard $\pm 15\text{ V}$ op amp supplies down to a single 3 V supply. Their output is compatible with RTL, DTL, and TTL as well as MOS circuits. Further, they can drive lamps or relays, switching voltages up to 50 V at currents as high as 50 mA .

Both the inputs and the outputs of the LM111 series can be isolated from system ground, and the output can drive loads referred to ground, the positive supply, or the negative supply. Offset balancing and strobe capability are provided and outputs can be wire-ORed.

Although slower than the $\mu\text{A}710$ (200 ns response time versus 40 ns), the devices are also much less prone to spurious oscillations. The LM111 series has the same pin configuration as the $\mu\text{A}710$ series.

FEATURES

- Operates from single 3 V supply (LM311B)
- Maximum input bias current: 150 nA (LM311: 250 nA)
- Maximum offset current: 20 nA (LM311: 50 nA)
- Differential input voltage range: $\pm 30\text{ V}$
- Power consumption: 135 mW at $\pm 15\text{ V}$
- High sensitivity: 200 V/mV
- Zero crossing detector

PIN CONFIGURATION

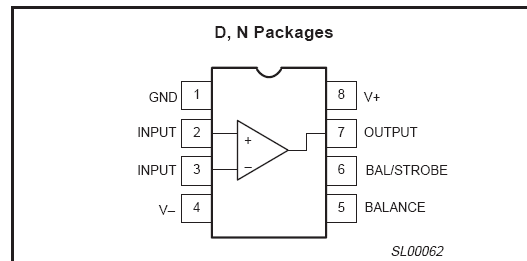


Figure 1. Pin Configuration

APPLICATIONS

- Precision squarer
- Positive/negative peak detector
- Low voltage adjustable reference supply
- Switching power amplifier

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE	DWG #
8-Pin Plastic Small Outline Package (SO)	$-55\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	LM111D	SOT96-1
8-Pin Plastic Dual In-Line Package (DIP)	$-55\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	LM111N	SOT97-1
8-Pin Plastic Small Outline Package (SO)	$-25\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	LM211D	SOT96-1
8-Pin Plastic Dual In-Line Package (DIP)	$-25\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	LM211N	SOT97-1
8-Pin Plastic Small Outline Package (SO)	$0\text{ }^{\circ}\text{C}$ to $+70\text{ }^{\circ}\text{C}$	LM311D	SOT96-1
8-Pin Plastic Dual In-Line Package (DIP)	$0\text{ }^{\circ}\text{C}$ to $+70\text{ }^{\circ}\text{C}$	LM311N	SOT97-1
8-Pin Plastic Small Outline Package (SO)	$0\text{ }^{\circ}\text{C}$ to $+70\text{ }^{\circ}\text{C}$	LM311BD	SOT96-1
8-Pin Plastic Dual In-Line Package (DIP)	$0\text{ }^{\circ}\text{C}$ to $+70\text{ }^{\circ}\text{C}$	LM311BN	SOT97-1

Voltage comparator

LM111/211/311/311B

EQUIVALENT SCHEMATIC

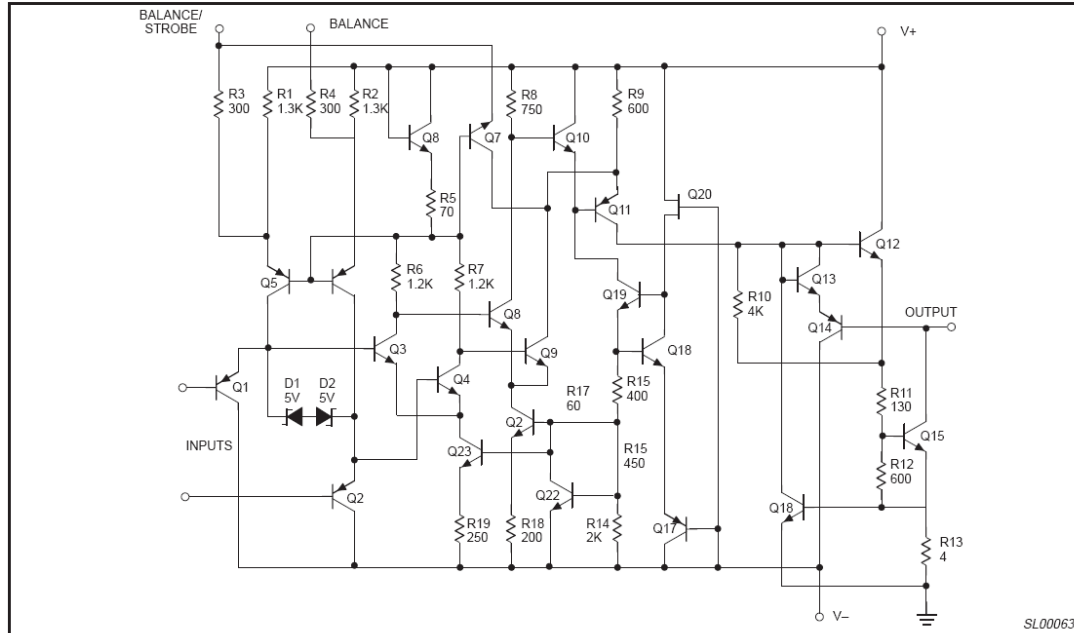


Figure 2. Equivalent Schematic

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V_S	Total supply voltage	36	V
	Output to negative supply voltage: LM111/LM211	50	V
	LM311/LM311B	40	V
	Ground to negative supply voltage	30	V
	Differential input voltage	± 30	V
V_{IN}	Input voltage ¹	± 15	V
$P_{D\ MAX}$	Maximum power dissipation, $T_{amb} = 25\ ^\circ\text{C}$ (still-air) ²		
	N package	1190	mW
	D package	780	mW
I	Output short-circuit duration	10	sec
T_{amb}	Operating ambient temperature range		$^\circ\text{C}$
	LM111	-55 to +125	$^\circ\text{C}$
	LM211	-25 to +85	$^\circ\text{C}$
	LM311/LM311B	0 to +70	$^\circ\text{C}$
T_{stg}	Storage temperature range	-65 to +150	$^\circ\text{C}$
T_{sld}	Lead soldering temperature (10 sec max)	230	$^\circ\text{C}$

NOTES:

- This rating applies for $\pm 15\text{ V}$ supplies. The positive input voltage limit is 30 V above the negative supply. The negative input voltage limit is equal to the negative supply voltage or 30 V below the positive supply, whichever is less.
- Derate above $25\ ^\circ\text{C}$, at the following rates:
N package at $9.5\text{ mW}/^\circ\text{C}$
D package at $6.2\text{ mW}/^\circ\text{C}$

Voltage comparator

LM111/211/311/311B

DC ELECTRICAL CHARACTERISTICS^{1, 2, 3, 6}

Over temperature range unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	LM111/LM211			LM311			LM311B			UNIT
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{OS}	Input offset voltage ³	$T_{amb} = 25\text{ }^{\circ}\text{C}$; $R_S \leq 50\text{ k}\Omega$		0.7	3.0		2.0	7.5		2.0	7.5	mV
I_{OS}	Input offset current ³	$T_{amb} = 25\text{ }^{\circ}\text{C}$		4.0	10		6.0	50		6	25	nA
I_{BIAS}	Input bias current	$T_{amb} = 25\text{ }^{\circ}\text{C}$		60	100		100	250		100	200	nA
A_V	Voltage gain	$T_{amb} = 25\text{ }^{\circ}\text{C}$		200			200			200		V/mV
	Response time ⁴	$T_{amb} = 25\text{ }^{\circ}\text{C}$		200			200			500		ns
V_{SAT}	Saturation voltage	LM111/211 $V_{IN} \leq -5\text{ mV}$; $I_{OUT} = 50\text{ mA}$ LM311/B $V_{IN} \leq -10\text{ mV}$; $I_{OUT} = 50\text{ mA}$ $T_{amb} = 25\text{ }^{\circ}\text{C}$		0.75	1.5		0.75	1.5		0.75	1.5	V
$I_{BAL/STR}$	Strobe on current	$T_{amb} = 25\text{ }^{\circ}\text{C}$		3.0			3.0			3.0		mA
$I_{LEAKAGE}$	Output leakage current ⁶	LM111/211 $V_{IN} \geq 5\text{ mV}$; $V_{OUT} = 35\text{ V}$ LM311/B $V_{IN} \geq 10\text{ mV}$; $V_{OUT} = 35\text{ V}$ $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_{STROBE} = 3\text{ mA}$ ($V_- = V_{GND} = -5\text{ V}$)		0.2	10		0.2	50		0.2	50	nA
V_{OS}	Input offset voltage ³	$R_S \leq 50\text{ k}\Omega$			4.0			10			10	mV
I_{OS}	Input offset current ³				20			70			50	nA
I_{BIAS}	Input bias current				150			300			250	nA
V_{IN}	Input voltage range	$V = \pm 15\text{ V}$ (Pin 7 may go to 5 V)	-14.5 to -14.7	13.8 to 13.0	13.0	-14.5 to -14.7	13.8 to 13.0	13.0	$V_- + 0.5$		$V_+ - 1.5$	V
V_{OL}	Saturation voltage ⁶	$V_+ \geq 4.5\text{ V}$, $V_- = 0\text{ V}$ LM111/211 $V_{IN} \leq -6\text{ mV}$; $I_{SINK} \leq 8\text{ mA}$ LM311/B $V_{IN} \leq -10\text{ mV}$; $I_{SINK} \leq 8\text{ mA}$		0.23	0.4		0.23	0.4		0.23	0.4	V
I_{OH}	Output leakage current	$V_{IN} \geq 5\text{ mV}$; $V_{OUT} = 35\text{ V}$		0.1	0.5							μA
I_{CC}	Positive supply current	$T_{amb} = 25\text{ }^{\circ}\text{C}$		5.1	6.0		5.1	7.5		1.6	3.5	mA
I_{EE}	Negative supply voltage	$T_{amb} = 25\text{ }^{\circ}\text{C}$		4.1	5.0		4.1	5.0				mA

NOTES:

1. This rating applies for $\pm 15\text{ V}$ supplies. The positive input voltage limit is 30 V above the negative supply. The negative input voltage limit is equal to the negative supply voltage or 30 V below the positive supply, whichever is less.
2. These specifications apply for $V_S = \pm 15\text{ V}$ and $0\text{ }^{\circ}\text{C} < T_{amb} < 70\text{ }^{\circ}\text{C}$ unless otherwise specified. With the LM211, however, all temperature specifications are limited to $-25\text{ }^{\circ}\text{C} \leq T_{amb} \leq +85\text{ }^{\circ}\text{C}$, and for the LM111 is limited to $-55\text{ }^{\circ}\text{C} < T_{amb} < +125\text{ }^{\circ}\text{C}$. The offset voltage, offset current, and bias current specifications apply for any supply voltage from a single 5 V supply up to $\pm 15\text{ V}$ supplies.
3. The offset voltages and offset currents given are the maximum values required to drive the output within a volt of either supply with 1 mA load. Thus, these parameters define an error band and take into account the worst case effects of voltage gain and input impedance.
4. The response time specified is for a 100 mV input step with 5 mV over-drive.
5. Do not short the strobe pin to ground; it should be current driven at 3 mA to 5 mA.
6. LM311B, all parameters are at $V_+ = 3\text{ V} \pm 10\%$; $V_- = \text{GND} = 0\text{ V}$.

Voltage comparator

LM111/211/311/311B

TYPICAL APPLICATIONS

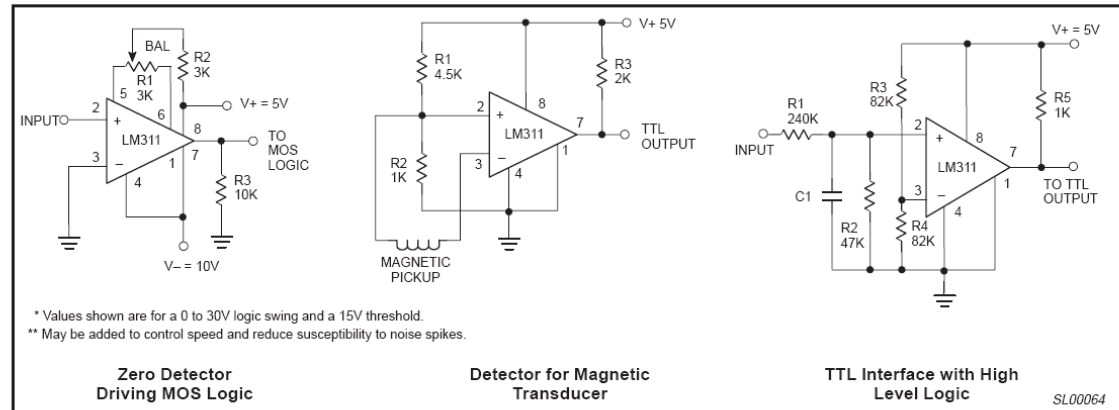


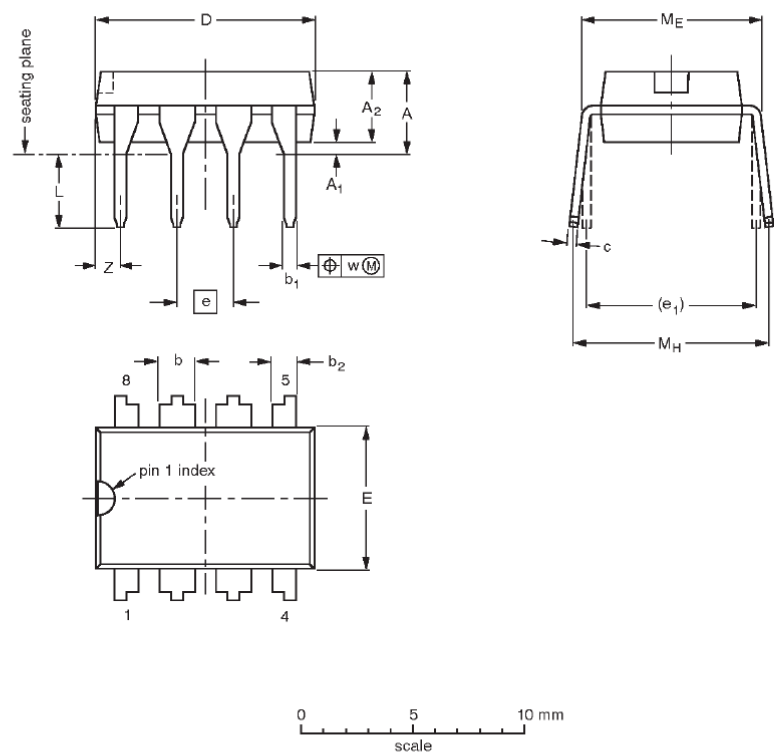
Figure 3. Typical Applications

Voltage comparator

LM111/211/311/311B

DIP8: plastic dual in-line package; 8 leads (300 mil)

SOT97-1




DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.14	0.53 0.38	1.07 0.89	0.36 0.23	9.8 9.2	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	1.15
inches	0.17	0.020	0.13	0.068 0.045	0.021 0.015	0.042 0.035	0.014 0.009	0.39 0.36	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.045

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

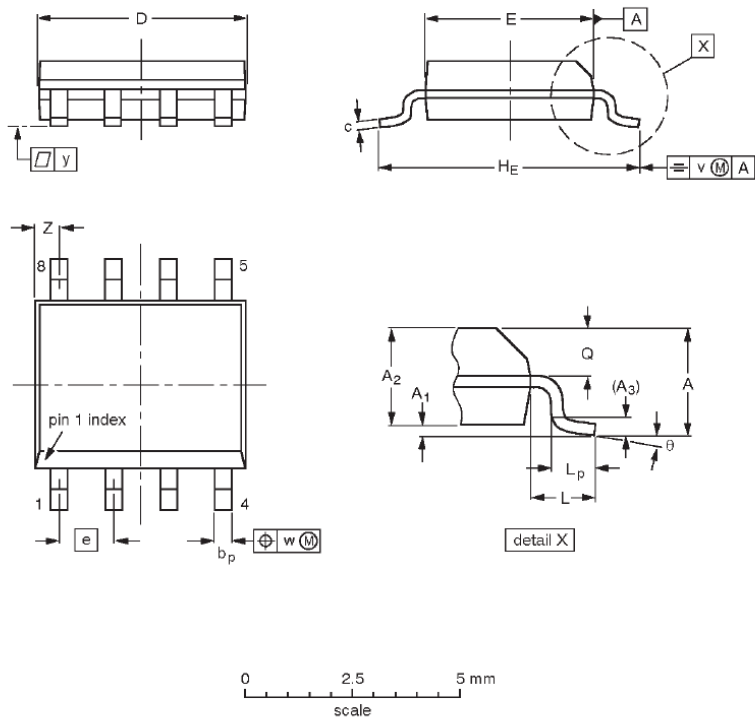
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Voltage comparator

LM111/211/311/311B

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1




DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.20 0.19	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT96-1	076E03	MS-012				97-05-22- 99-12-27

Voltage comparator

LM111/211/311/311B

Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definitions
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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